

Schottky barrier diode

RB521G-30

●Application

Rectifying small power

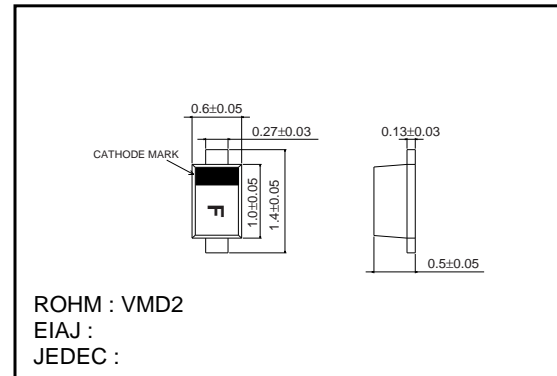
●Features

- 1) Ultra small mold type. (VMD2)
- 2) High reliability

●Construction

Silicon epitaxial planer

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_o	100	mA
Forward current surge peak *	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60Hz, 1cyc.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.350	V	$I_F=10\text{mA}$
Reverse current	I_R	–	–	10	μA	$V_R=10\text{V}$

* Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

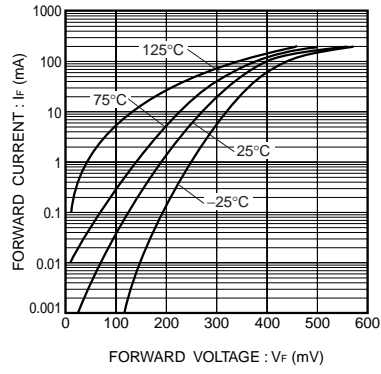


Fig.1 Forward characteristics

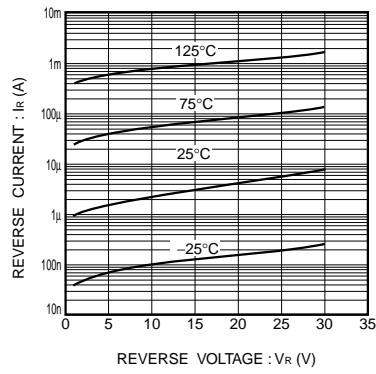


Fig.2 Reverse characteristics

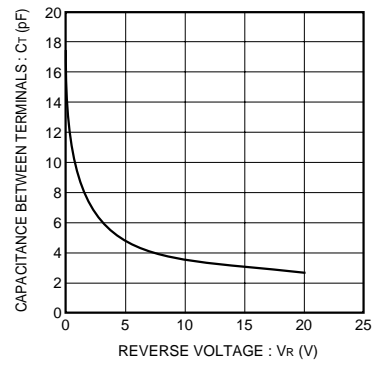


Fig.3 Capacitance between terminals characteristics